

IN THE CLAIMS

1-20. (Cancelled)

21. (Original) A method for fabricating a liquid crystal display device comprising:
forming a first metal seed layer on a glass substrate;
depositing a first metal layer using an electric plating method;
patterning the first metal seed layer and the first metal layer to form a gate line and a gate electrode;
forming a gate insulating film on an entire surface including the gate line;
forming a semiconductor layer on the gate electrode;
forming a second metal seed layer on the entire surface including the semiconductor layer;
depositing a second metal layer using the electric plating method;
patterning the second metal seed layer and the second metal layer to form a data line crossing the gate line and source/drain electrodes on the semiconductor layer; and
forming a pixel electrode connected with the drain electrode, on a passivation film formed on the entire surface including the data line.

22. (Original) The method of claim 21, wherein the electric plating method includes the steps of:

arranging the substrate provided with the first and second metal seed layers in a tub containing an electrolytic solution and applying a negative potential to the substrate to remove a metal oxide film on surfaces of the first and second metal seed layers; and

providing a deposition solution to the tub and applying the negative potential to the substrate to deposit a metal on the first and second metal seed layers.

23. (Original) The method of claim 22, wherein the electric plating method is performed in such a manner that pH and potential of the electrolytic solution are controlled.

24. (Original) The method of claim 22, wherein the step of removing the metal oxide film and the step of depositing the metal are performed within different chambers in the tub.

25. (Original) The method of claim 22, wherein the electrolytic solution reduces the metal oxide film formed on the surfaces of the first and second metal seed layers to metal layers.

26. (Original) The method of claim 22, wherein the electric plating method is performed at a temperature of about 25~100°C.

27. (Original) The method of claim 22, wherein the electric plating method is performed within the range of current of about 10~100 μ A.

28. (Original) The method of claim 22, wherein the deposition solution includes a metal which is the same as the metal of the first and second metal seed layer and does not react with the electrolytic solution.

29. (Original) The method of claim 21, further comprising the steps of forming another substrate to oppose the glass substrate and forming a liquid crystal between the two substrates.

30. (Original) The method of claim 21, wherein the first and second metal seed layers are formed of a metal material containing metal of the first and second metal layers.

31. (Original) The method of claim 21, wherein the first and second metal layers are formed of any one of Cu, Al, Cr, Mo, W, or an Al alloy.